

	Type	Hits	Search Text	DBs	Time Stamp
1	BRS	696	(438/400).ccls. and @ad<=20011206	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/17 11:22
2	BRS	6	((438/400).ccls. and @ad<=20011206) and ONO	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/17 11:26
3	BRS	0	@ad<=20011206 and 'ONO structure' with 'buffer layer'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/17 12:35
4	BRS	290	@ad<=20011206 and 'ONO structure'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/17 12:01
5	BRS	160	@ad<=20011206 and 'Oxide' with 'SiON' with 'SiN' with 'SiON' with 'Oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/17 12:31
6	BRS	3	@ad<=20011206 and 'ONO structure' and 'buffer layer'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/17 12:40
7	BRS	1	@ad<=20011206 and 'multi dielectric layer' and 'memory'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/17 12:43
8	BRS	26	@ad<=20011206 and 'multi' adj 'dielectric' and 'memory'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/17 12:47
9	BRS	0	@ad<=20011206 and 'O-SiON-N-SiON-O'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/17 12:49
10	BRS	1393	@ad<=20011206 and oxide and SiON and Nitride and SiON and oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/17 12:55
11	BRS	0	@ad<=20011206 and oxide adj SiON adj Nitride adj SiON adj oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/17 12:56
12	BRS	300	@ad<=20011206 and 'oxide' with 'SiON' with 'nitride' with 'SiON' with 'oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/17 14:31
13	BRS	107	(@ad<=20011206 and 'oxide' with 'SiON' with 'nitride' with 'SiON' with 'oxide') and memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/17 13:49
14	BRS	540	@ad<=20011206 and (438/778).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/17 14:32